

wherein R₁ represents phenylene or biphenylene; R₂ represents hydrogen or alkyl having up to four carbon atoms; and n is a positive number from 1 to 10 as an average;

an inorganic filler (C);

a curing accelerator (D);

a silane coupling agent (E); and

Compound (F) containing two and more hydroxyl groups on combined with each of adjacent carbon atoms ~~comprising in~~ an aromatic ring.

2. (Original) The resin composition for encapsulating a semiconductor chip according to Claim 1, wherein the resin composition comprises said Compound (F) in more than or equal to 0.01 wt%.

3. (Original) The resin composition for encapsulating a semiconductor chip according to Claim 1, wherein the resin composition comprises said silane coupling agent (E) in 0.01 wt% to 1 wt% both inclusive.

4. (Currently Amended) The resin composition for encapsulating a semiconductor chip according to Claim 1, wherein said compound (F) contains two hydroxyl groups on combined with each of adjacent carbon atoms ~~comprising in~~ said aromatic ring.

5. (Previously Presented) he resin composition for encapsulating a semiconductor chip according to Claim 1, wherein the aromatic ring is a naphthalene ring in Compound (F).

6. (Currently Amended) The resin composition for encapsulating a semiconductor chip according to Claim 5, wherein said Compound (F) contains two hydroxyl groups on combined with each of adjacent carbon atoms ~~comprising in~~ said naphthalene ring.

7. (Original) The resin composition for encapsulating a semiconductor chip according to Claims 1, wherein the resin composition comprises said inorganic filler (C) in 84 wt% to 90 wt% both inclusive.

8. (Previously Presented) A semiconductor device wherein a semiconductor chip is encapsulated by the resin composition according to Claim 1.

9. (Previously Presented) The resin composition for encapsulating a semiconductor chip according to Claim 1,

wherein said inorganic filler (C) is present in an amount of 84 wt% to 90 wt% both inclusive,

said silane coupling agent (E) is present in an amount of 0.01 wt% to 1 wt% both inclusive, and

said Compound (F) is present in an amount of 0.01 wt% to 0.5 wt% both inclusive.